

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	30	V
Gate-Source Voltage			V <sub>GSS</sub>	±25	V
Drain Current (Note 6)	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	9.0	A
		T <sub>A</sub> = +70°C		6.75	
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	40	A

**Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P <sub>D</sub>	1.7	W
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	73	°C/W
Total Power Dissipation (Note 6)	P <sub>D</sub>	2.5	W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	50	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250µA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	µA	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
		—	—	±1	µA	V <sub>GS</sub> = ±25V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	1	—	2.1	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250µA
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	—	15.7 26.4	18 30	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 9A V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 7A
Forward Transconductance	g <sub>fs</sub>	—	5.8	—	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 9A
Diode Forward Voltage	V <sub>SD</sub>	0.5	0.7	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 2.1A
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	—	741	—	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	124	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	95	—	pF	
Gate Resistance	R <sub>G</sub>	0.30	0.88	2.5	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz
<b>SWITCHING CHARACTERISTICS (Note 8)</b>						
Total Gate Charge	Q <sub>g</sub>	—	7.6 16.7	12 25	nC	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 9A
Gate-Source Charge	Q <sub>gs</sub>	—	1.9	—		V <sub>DS</sub> = 15V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 9A
Gate-Drain Charge	Q <sub>gd</sub>	—	5.2	—		
Turn-On Delay Time	t <sub>d(on)</sub>	—	4.0	—	ns	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 15V, R <sub>L</sub> = 15Ω, R <sub>G</sub> = 6Ω
Rise Time	t <sub>r</sub>	—	4.4	—		
Turn-Off Delay Time	t <sub>d(off)</sub>	—	23.0	—		
Fall Time	t <sub>f</sub>	—	9.4	—		

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

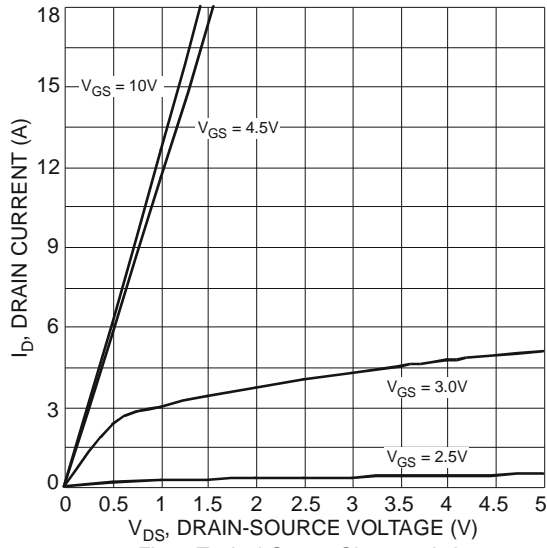


Fig. 1 Typical Output Characteristic

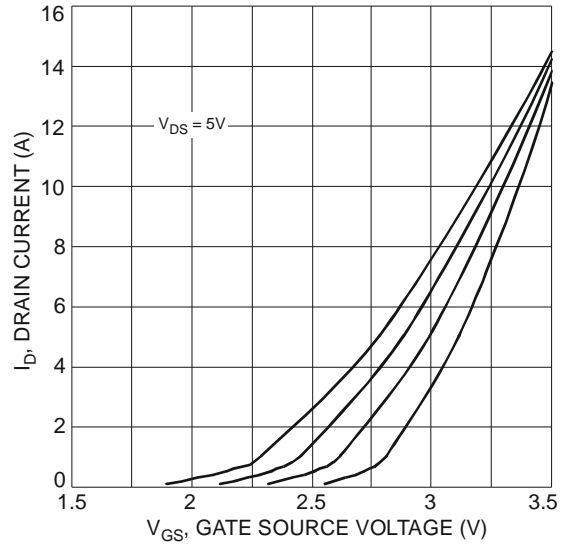


Fig. 2 Typical Transfer Characteristics

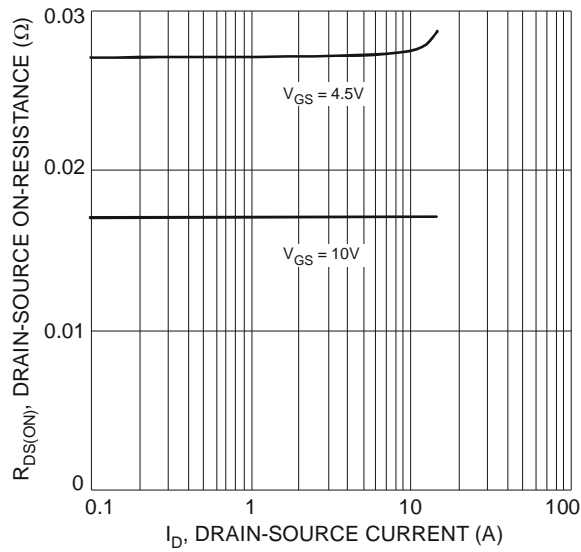


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

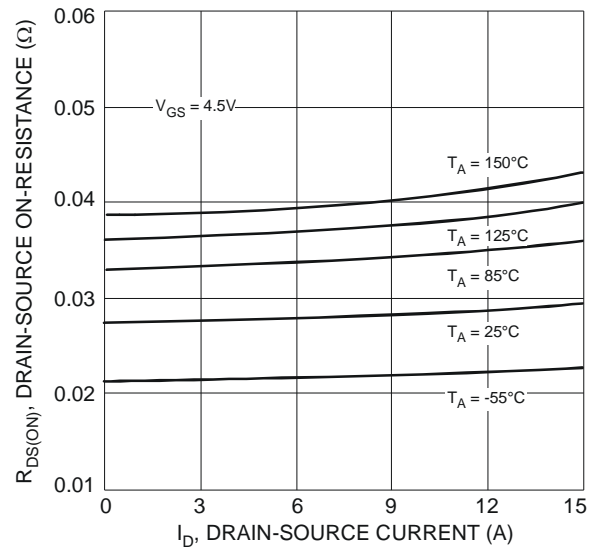


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

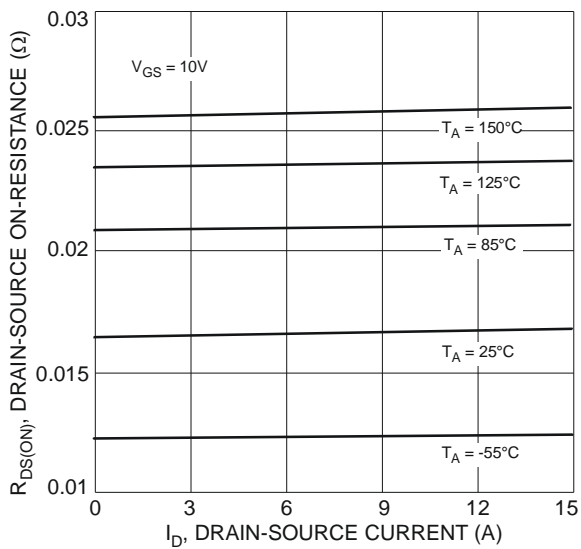


Fig. 5 Typical On-Resistance vs. Drain Current and Temperature

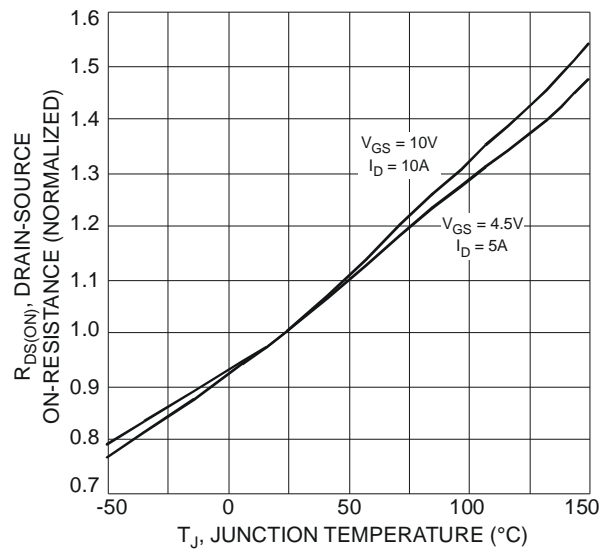


Fig. 6 On-Resistance Variation with Temperature

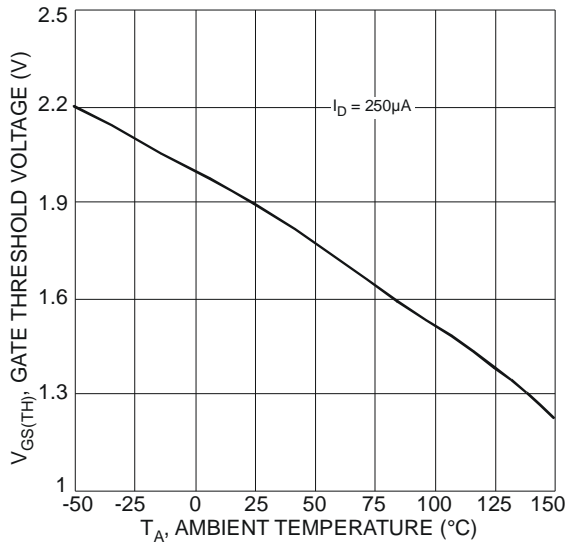


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

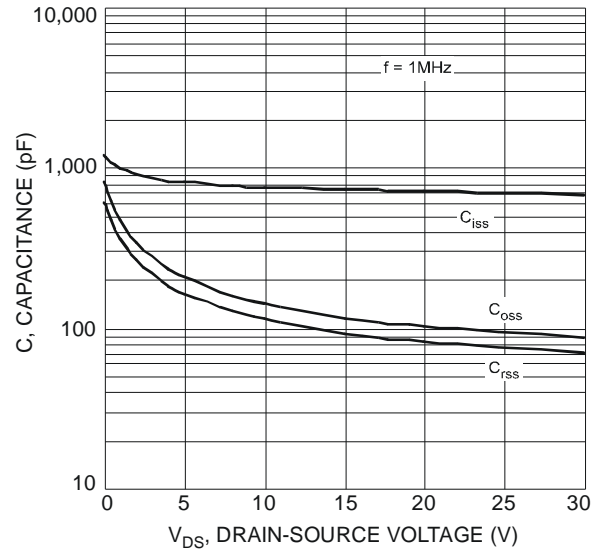


Fig. 8 Total Capacitance

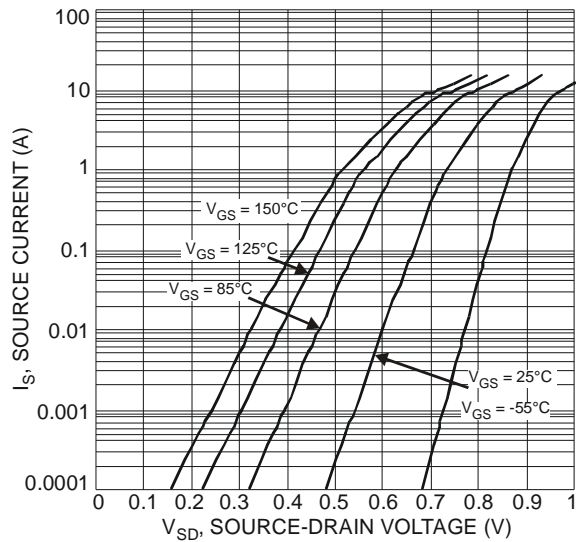


Fig. 9 Diode Forward Voltage vs. Current

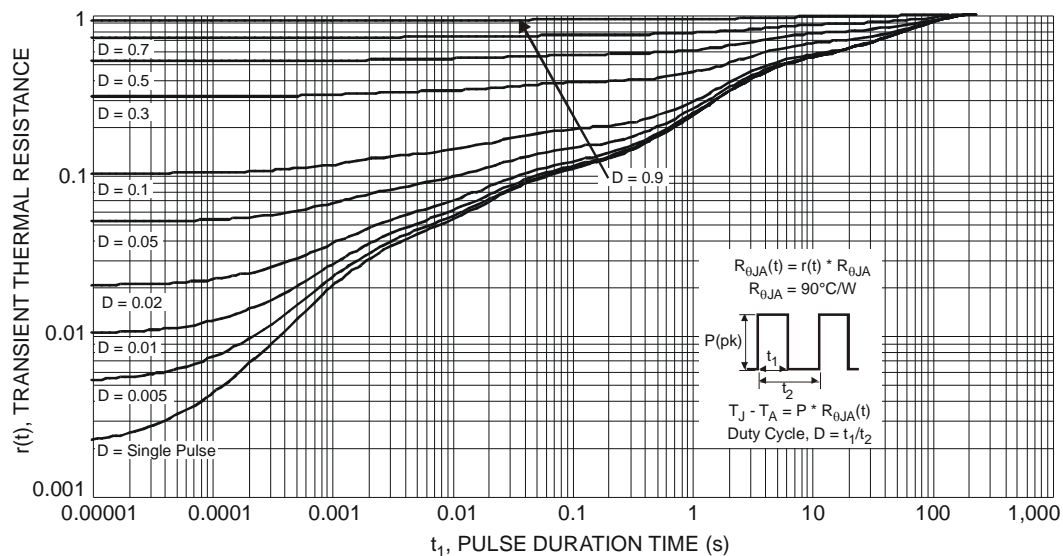
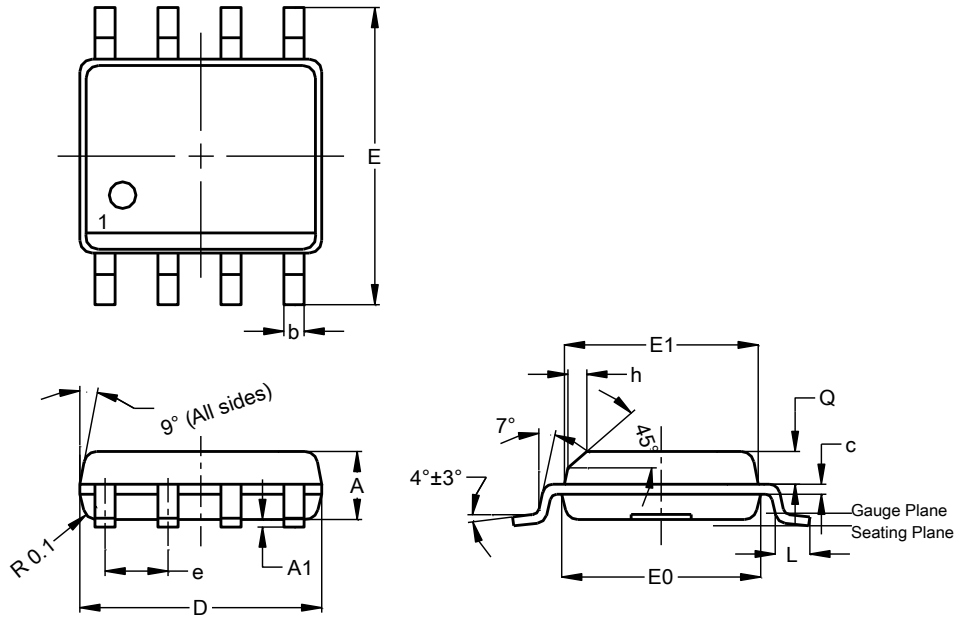


Fig. 10 Transient Thermal Response

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

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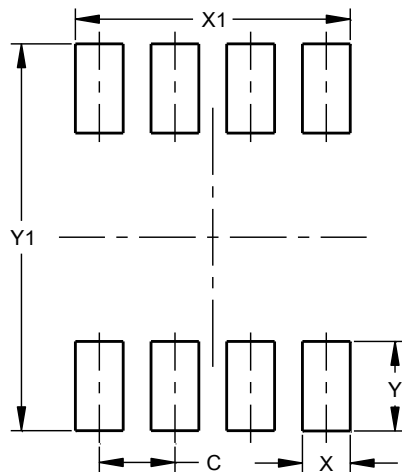


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Dim	Min	Max	Typ
A	1.40	1.50	1.45
A1	0.10	0.20	0.15
b	0.30	0.50	0.40
c	0.15	0.25	0.20
D	4.85	4.95	4.90
E	5.90	6.10	6.00
E1	3.80	3.90	3.85
E0	3.85	3.95	3.90
e	--	--	1.27
h	-	--	0.35
L	0.62	0.82	0.72
Q	0.60	0.70	0.65
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

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Dimensions	Value (in mm)
C	1.27
X	0.802
X1	4.612
Y	1.505
Y1	6.50

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